1. General description

NPN high-voltage low V_{CEsat} transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9215Z

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- Medium power SMD plastic package
- AEC-Q101 qualified

3. Applications

- · LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|---------------------------|-----------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| V _{CEO} | collector-emitter voltage | open base | - | - | 150 | V |
| I _C | collector current | | - | - | 2 | Α |
| h _{FE} | DC current gain | V_{CE} = 10 V; I_{C} = 100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C | 100 | 240 | - | |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|----------------------------------|----------------|
| 1 | В | base | 4 | C; C |
| 2 | С | collector | | В |
| 3 | E | emitter | | D — N |
| 4 | С | collector | □ 1 □ 2 □ 3 | Ė |
| | | | SC-73 (SOT223) | sym016 |

6. Ordering information

Table 3. Ordering information

| Type number | | | |
|-------------|------|-----------------------------------------------------------------------------------------------------------------|---------|
| | Name | Description | Version |
| PBHV8215Z | | plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body | SOT223 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBHV8215Z | V8215Z |

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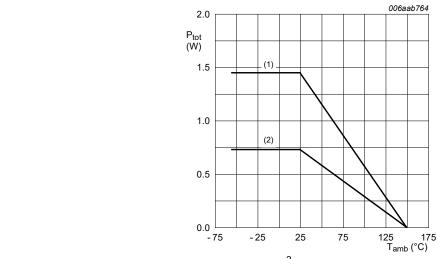
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V _{CBO} | collector-base voltage | open emitter | | - | 350 | V |
| V_{CEO} | collector-emitter voltage | open base | | - | 150 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | 6 | V |
| I _C | collector current | | | - | 2 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | 4 | Α |
| I _{BM} | peak base current | | | - | 500 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 1.45 | W |
| | | | [2] | - | 0.73 | W |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--------------------------------------------------|-------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from | in free air | [1] | - | - | 85 | K/W |
| | junction to ambient | | [2] | - | - | 170 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 15 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

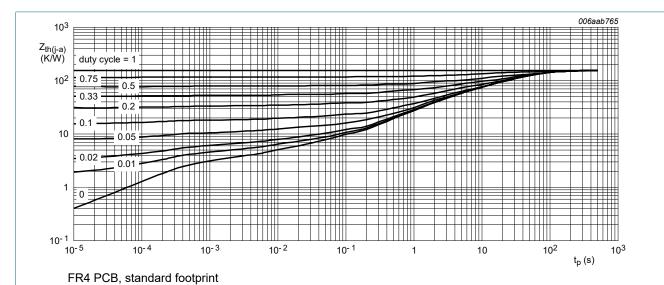


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

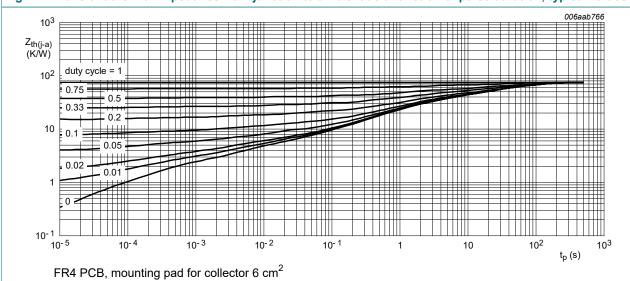


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|-----------------------------------------|--------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| I _{CBO} | collector-base cut-off | V _{CB} = 120 V; I _E = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| current | | V _{CB} = 120 V; I _E = 0 A; T _j = 150 °C | - | - | 10 | μA |
| I _{EBO} | emitter-base cut-off current | V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| I _{CES} | collector-emitter cut-off current | V _{CE} = 120 V; V _{BE} = 0 V; T _{amb} = 25 °C | - | - | 100 | nA |
| h _{FE} | DC current gain | V_{CE} = 10 V; I_{C} = 100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 100 | 240 | - | |
| | | V_{CE} = 10 V; I_{C} = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 100 | 230 | - | |
| | | V_{CE} = 10 V; I_{C} = 1.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 90 | 210 | - | |
| | | V_{CE} = 10 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 55 | 130 | - | |
| V _{CEsat} | collector-emitter saturation voltage | I_C = 100 mA; I_B = 20 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 15 | 30 | mV |
| | | I_C = 1 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 90 | 170 | mV |
| | | I_C = 1.5 A; I_B = 300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 130 | 220 | mV |
| | | I_C = 2 A; I_B = 400 mA; pulsed; $t_p \le$ | - | 170 | 280 | mV |
| R _{CEsat} | collector-emitter saturation resistance | 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | - | 85 | 140 | mΩ |
| V_{BEsat} | base-emitter saturation voltage | | - | 1 | 1.2 | V |
| t _d | delay time | V _{CC} = 6 V; I _C = 0.5 A; I _{Bon} = 0.1 A; | - | 20 | - | ns |
| t _r | rise time | I _{Boff} = -0.1 A; T _{amb} = 25 °C | - | 280 | - | ns |
| t _{on} | turn-on time | | - | 300 | - | ns |
| t _s | storage time | | - | 2165 | - | ns |
| t _f | fall time | | - | 275 | - | ns |
| t _{off} | turn-off time | | - | 2440 | - | ns |
| f _T | transition frequency | V _{CE} = 10 V; I _C = 10 mA; f = 100 MHz; T _{amb} = 25 °C | - | 33 | - | MHz |
| C _c | collector capacitance | V _{CB} = 20 V; I _E = 10 mA; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C | - | 17 | - | pF |
| C _e | emitter capacitance | V _{EB} = 0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C | - | 500 | - | pF |

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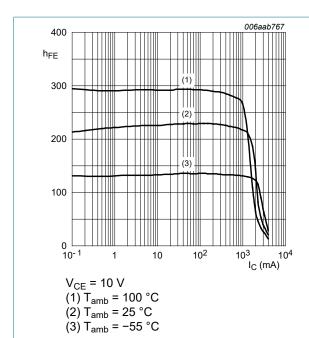


Fig. 4. DC current gain as a function of collector current; typical values

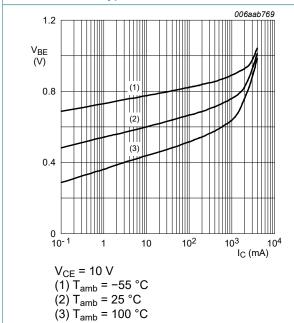


Fig. 6. Base-emitter voltage as a function of collector current; typical values

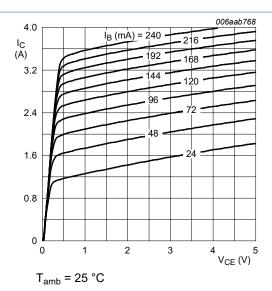
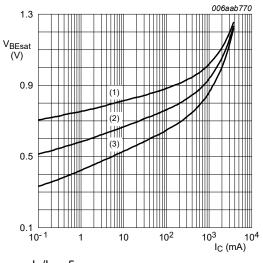


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_{C}/I_{B} = 5$ (1) $T_{amb} = -55 \,^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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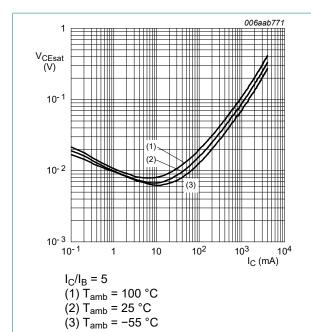


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

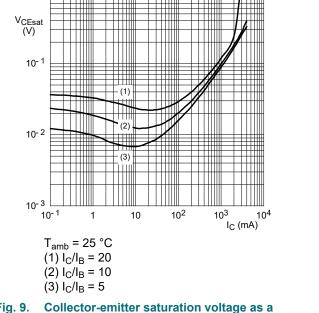


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

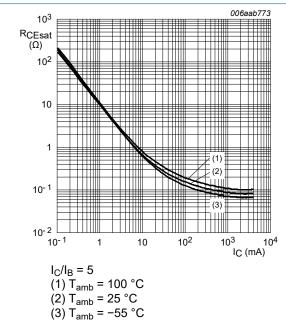


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

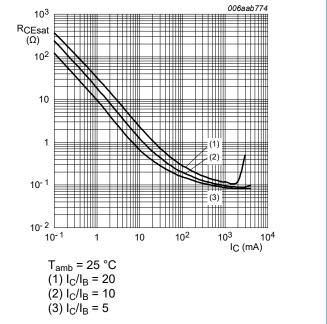
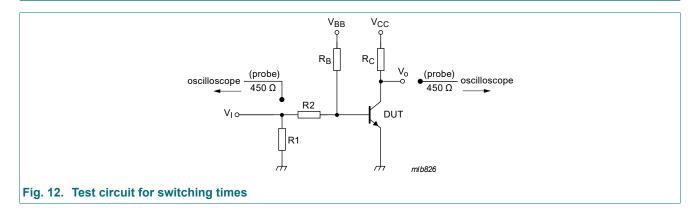


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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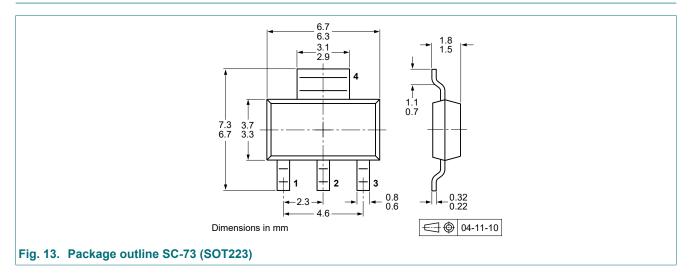
11. Test information



Quality information

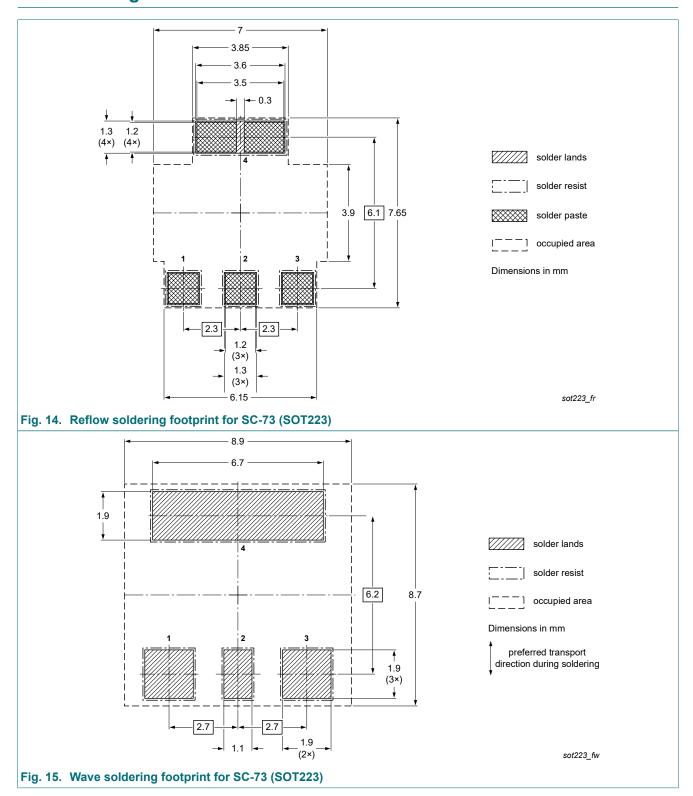
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | |
|----------------|----------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|-------------|--|
| PBHV8215Z v.2 | 20230712 | Product data sheet | - | PBHV8215Z_1 | |
| Modifications: | Nexperia. • Legal texts ha | his data sheet has been redesigned to comply with the identity guidelines of ve been adapted to the new company name where appropriate. ng information" removed. | | | |
| PBHV8215Z_1 | 20091111 | Product data sheet | - | - | |

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
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